



# **Review Paper on Power Efficient Hybrid D-Flip Flop**

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**ABSTRACT:** In nanometer CMOS technologies leakage power has become a serious concern and is a very important issue in hardware and software VLSI design. The leakage power increases as technology is scaled down. Low power flip-flops play a vital role for the design of low-power digital systems. In this paper several different flip flop topologies are analyzed and power efficient flip flop method is proposed. This paper presents survey on low power hybrid dual dynamic flip flop (DDFF) and embedded logic module (DDFF-ELM) based on DDFF. This survey concludes that ultra low leakage CMOS structure called as sleepy stack inverter pair method which is efficient in leakage power reduction for design of low power hybrid flip flop thus providing circuit designer with new choice to handle leakage power problem.

**KEYWORDS:** CMOS, DDFF, DDFF-ELM, sleepy-stack, power dissipation

## **I. INTRODUCTION**

In nanoscale technology leakage is a serious problem particularly for CMOS circuits. According to the International Technology Roadmap for Semiconductors (ITRS) leakage power consumption may come to dominate total chip power consumption as technology feature size shrinks. With the growing trend towards portable computing and wireless communication the need of low power increases day-by-day. As Flip flop and latches are the major source of power consumption in synchronous system thus studies of low power and high performance flip flop is important.

The industry for low power consumer electronic products is booming with a rapidly expanding market. As Flip-flops are common building blocks and are frequently used in digital VLSI circuits. These are used as starting, intermediate and ending part in the systems. They consume large amount of power because these are operated at system operating frequency. Thus a careful design of low power flip flop is important for Low power VLSI system.

Sequential logic circuits such as registers, memory element counters etc are mostly used in implementation of Very Large Scale Integration (VLSI) Circuits. The CMOS technologies approach has its fundamental physical limits. However, when scaling comes down to submicron level or Nano level many problems occur. As the feature size shrinks, upto  $0.09\mu$  and  $0.065\mu$ , static power has become a great challenge for current and future technologies and if physical gate length is reduced to below 65nm several device level effects such as short channel effect and exponential increase in leakage current. The four main sources of leakage current in a CMOS transistor are i) Reverse-biased junction leakage current ii) Gate induced drain leakage iii) Gate direct tunnelling leakage and iv) Sub-threshold (weak inversion) leakage current. The sub-threshold leakage current being the most leading amongst all the leakage current sources which becomes very challenging for research in current and future silicon technologies.

The flip-flop is considered to be the most essential memory cell in the vast majority of digital circuits. Thus, we design a new dual dynamic node hybrid flip-flop (DDFF) and dual dynamic node hybrid flip-flop with embedded logic module (DDFF-ELM) by using sleepy stack inverter pair. Thus the sleepy stack inverter pairs are efficient in leakage power reduction and overall power dissipation as technology scales down to 90nm and below.

Flip flop is widely used in synchronous sequential circuits and it can be designed in two logic styles namely static and dynamic. Dynamic style exhibits high speed and less area where static design style exhibits less power. Thus here we consider hybrid flip flop which possess advantage of both static and dynamic design style. The dynamic style is present at the input side and static style is present at the output side of flip-flop design.

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Fig. 1 Design Parameters

The power is rising as the most critical and vital issues in system on chip design today and management of power in every category of design is becoming an urgent problem. In early 1970's, providing high speed operation with minimum area were main aim of design. Many design tools are concentrated to achieve these goals shown in Fig 1

In CMOS VLSI circuits, power dissipation is basically due to the three important and major components: dynamic, static and short circuit.

$$P = P_{\text{dynamic}} + P_{\text{short circuit}} + P_{\text{leakage}}$$

Dynamic power dissipation is due to switching activity and short circuiting.

$$P_d = f C V_{dd}^2$$

Short circuit power is caused by the finite rise and fall time of input signals, resulting in both the pull up network and pulldown network to be ON for a short while.

$$P_s = I_{\text{leakage}} V_{dd}$$

Leakage is the leakage power. When supply voltage scaling down, the threshold voltage also decreases to maintain performance. However, this leads to the exponential growth of the sub threshold leakage current. Sub threshold leakage is the dominant leakage

$$P_{\text{leakage}} = I_{\text{leakage}} V_{dd}$$

## II. PREVIOUS WORK DONE

In the design of various sequential circuits, a major challenge is the Design of an efficient low power hybrid D-flip-flop. Thus in many papers different flip flops are proposed overcoming the drawbacks of their presiding designs and analyze power of different dual dynamic node hybrid flip flop. Kalarikkal Absel have designed low-Power dual dynamic node pulsed hybrid flip-flop. In this paper first they have compared and discussed about some existing static and dynamic flip-flop such as Hybrid latch flip-flop (HLFF), semi dynamic flip-flop (SDFF) and cross charge controlled flip-flop (XCFF). They studied and designed two different kinds of pulsed hybrid flip flop which is called as dual dynamic node flip flop (DDFF) and a novel embedded logic module (DDFFELM) and both of them eliminate the drawbacks of unwanted transitions in cross charge controlled flip-flop (XCFF) when data input is stable at 0. Their design carried out comparison of low power pulsed hybrid flip-flop and gives 29% and 7% reduction in total power dissipation compared to SDFF and XCFF at 50% data activity [1].

Meghana Pelleti has proposed low power and low area dual dynamic node hybrid flip-flop using 120 nm CMOS technology. In this paper first they have compared and discussed about some existing flip-flops such as HLFF, SDFF and XCFF. Drawbacks of this XCFF flip-flop were unwanted transitions and due to this unwanted transitions power dissipation problem will occur. Comparison of the dual dynamic node hybrid flip flop (DDFF) showed that it exhibits lower power dissipation along with area [2].

Karthika have designed Power efficient hybrid pulsed flip-flop (HPFF) with embedded logic module (HPFF-ELM) based on transmission gate scheme. They compared three existing designs of dual dynamic node flip-flop such as Conditional data mapping flip-flop (CDMFF), cross charge controlled flip flop (XCFF), Dual dynamic flip-flop (DDFF) and DDFF-ELM with the proposed design of the HPFF and HPFF-ELM. The HPFF consists of less number of transistors by using transmission gate instead of back-to-back inverters in the previous XCFF and DDFF architectures. Thus the layout area and delay consumed by the design is reduced. Also the number of transistors used by HPFF-ELM is very less when compared with DDFF-ELM and SDFF-ELM. Thus the layout area and the delay are also reduced. The power dissipation produced after embedding logic functions is decreased dramatically. A comparison of the proposed



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flip-flop with the conventional flip-flops showed that it exhibits lower power dissipation along with speed performances. [3].

Varuna RTV have designed Dual Dynamic Edge Triggered Low Power Flip-Flop Featuring ELM where edge triggering is provided by the NMOS. The proposed design reduces the power consumption up to 20% compared to the conventional flip-flops. Also A high speed ring counter using digital CMOS gate logic components by the DDFF structure is also designed which is well suited for modern high performance circuits [4]. Omid Sarbishei have proposed An Efficient Implementation of Flip-Flops with Embedded Logic. This paper presents several efficient architectures of dynamic/static edge-triggered flip-flops with a compact embedded logic. The overlap-based DDFF is proposed in which lookup table is implemented in pull down network (PDN). Also the overlap-based logic cells become more efficient when the complexity of their embedded logic function increases. The main advantage is that this approach improves static power consumption due to the reduction of p-type MOS (pmos) transistors and voltage swing in internal nodes, which makes it even more efficient in below 0.18  $\mu$ m CMOS technologies [5].

R Siva Kumar have designed Low-Power Efficient Double Edge Trigger Flip Flop using Tanner EDA tool. In Double edge triggered Flip-Flops data signal changes on both the rising and falling clock edges. Thus, results in low clock swing and it leads to lower power consumption. The proposed design solves the long discharging path problem in conventional explicit type pulse-triggered FF (P-FF). In this paper, a new low power DDFF was proposed. Also 4-b ring counter using DDFF is designed. These results showed that the proposed DDFF is efficient in terms of power, delay and power delay product [6].

Hinamalviya has compared Various Leakage Power Reduction Techniques For CMOS Circuit Design such as sleep mode approach, stack approach, sleepy keeper and sleepy stack method. The sleepy keeper method achieves leakage power reduction equivalent to the sleep and other approaches with the advantage of maintaining exact logic state. But the main disadvantage is that, sleepy keeper causes additional dynamic power consumption, approximately 15% more than the base case. The sleepy stack well-known low leakage techniques which have a combined structure of forced stack, sleep transistor which achieves ultra-low leakage power consumption while retaining state. Their design carried out comparison of sleepy stack method of 2 input NAND gate that have achieved dynamic power reduction up to 20.03%, static power reduction up to 65.91%, delay increment up to 101.5% and PDP up to 40.20% [7].

Shahriar Jalal Nibir have proposed A New Leakage Reduction Method for Ultra Low Power VLSI Design for Portable Devices. They compared existing designs of Leakage power reduction such as Sleep Transistor Technique, Sleepy Stack Technique, Sleepy Keeper Technique, Dual Sleep Technique, Dual Stack Technique. The comparative analysis showed that the stacked sleep transistor offers superior static and dynamic power reduction [8].

Tripti Mehta have proposed various Low Power Consumption Techniques in a VLSI Circuit such as sleep, stack, sleepy keeper and reverse body bias with sleep and stack. Their simulation results of power consumption are done on a TANNER EDA tool at 90 nm technology which showed that the proposed XNOR circuit using reverse body with sleep and stack achieves up to 60% less power consumption as compared to the base case [9].

Jun Cheol Park have proposed Sleepy Stack Leakage Reduction. He proposed ultra-low leakage CMOS circuit structure which is called "sleepy stack". Sleepy stack method is state-saving technique where circuit state (present value) is retained and thus achieves ultra-low leakage power consumption. A state-saving technique has an advantage over a state-destructive technique is that the circuitry can immediately resume operation at a point much later in time without having to somehow regenerate state [10]. Sleepy Stack approach can achieve more power savings with the advantage of less delay as compared to the forced stack technique.

### III. COMPARISON OF LEAKAGE REDUCTION TECHNIQUES

Leakage current is a major concern for low-power, high performance digital CMOS circuits thus various methods are used to reduce leakage current but it is limited up to the certain application. The Base Case (conventional CMOS) contains only the PMOS network and the NMOS network and therefore no reduction in leakage current. It is a state saving technique and has a minimum area requirement. The Forced stack technique is easy to implement and thus useful for leakage savings but at the same time propagation delay increases. Whereas the Sleep transistor method provides good reduction in leakage power, but it is a state destructive technique (current Boolean output value of the circuit might be lost). The sleepy stack method is State Saving Technique also it has advantage over forced stack technique is that it requires less delay compared to forced stacking. In active mode, sleepy stack approach is suitable for faster

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circuit operation. Sleepy stack approach is used to reduce leakage power as well as average power drastically thus useful to enhance power performance.

## IV. SLEEPY STACK STRUCTURE

In our proposed approach, leakage power reduction technique name as “sleepy stack.” The sleepy stack technique has a combined structure of the forced stack technique and the sleep transistor technique. The Sleepy Stack Technique combines the Stack & Sleep techniques. In Fig 2 the existing transistors are divided into two half size transistors in the Sleepy Stack technique like as Stack technique. If dual-V<sub>th</sub> values are available, high-V<sub>th</sub> transistors are used. Between the divided transistors one of sleep transistor will be added in parallel.

Fig 3 shows stack technique where the existing transistor are breaking down into two half size transistors. Stacked transistors suppress leakage current while saving state & Sleep transistors are turned off during sleep mode. Thus we reduce the leakage power and overall total power at high speed by replacing the CMOS inverter pair by sleepy stack inverter pair. Leakage power reduction can be classified into two ways.

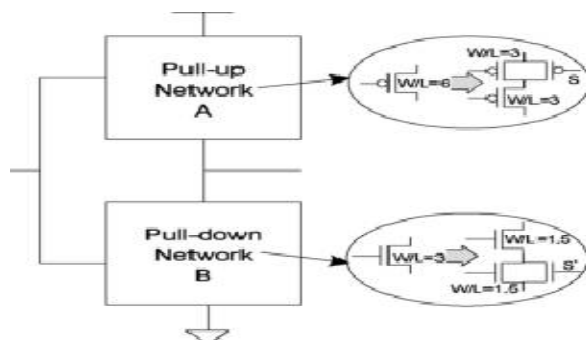


Fig. 2 Sleepy Stack Structure [10]

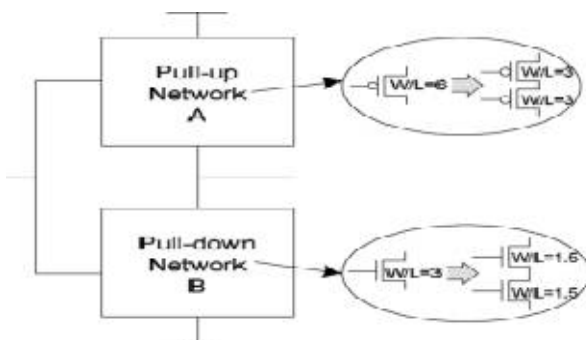


Fig. 3 Forced Stack structure [10]

First is State destructive technique which does not retain exact logic state when the circuit is switched to the other modes and second is the state saving technique which retains the exact logic state. State-destructive techniques cutoff transistor (pull-up or pull down or both) networks from supply voltage or ground using sleep transistors. These types of techniques are also called gated-V<sub>dd</sub> and gated-G<sub>nd</sub> (note that a gated clock is generally used for dynamic power reduction) [10].

A state-saving technique has an advantage over a state-destructive technique in that with a state-saving technique the circuitry can instantly resume operation at a point much later in time without having to somehow regenerate state. We characterize each low-leakage technique according to this criterion [10]. Thus this sleepy stack inverter pair is a state-saving technique which is used for leakage power reduction of flip flop in sleep mode and total power is also reduced by running the flip flop in active mode.

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## V. PROPOSED WORK

In Dual Dynamic Node Hybrid Flip-Flop (DDFF), there are two nodes in the circuit among which one is purely dynamic and another is pseudo-dynamic. So, it is called as dual dynamic. Fig. 4 shows schematic of DDFF. As it is having dynamic front end and static output, it is hybrid in nature. The operation of the flip-flop can be divided into two phases. First is evaluation phase, when CLK is high, and the pre-charge phase, when CLK is low. The proposed DDFF architecture acts both as static and dynamic circuits. Thus the operation of DDFF is based on dynamic logic principles. The flip flop requires two phase to operate based on the clock input to the circuit.

In evaluation phase- The architecture exhibits negative setup time since the short transparency period is defined by the 1-1 overlap CLK and CLK B allows the data to be sampled even after the rising edge of CLK before CLK B falls low. As CLK falls low, the circuit enters in the pre-charge phase and node X1 pulled high through PM0, switching the state of INV1-2. During this period node X2 is not actively driven by any transistor, it stores the charge dynamically. If D is low (prior to the overlap period), node X1 remains high and node X2 pulled low through NM3 as the CLK goes high. Thus, node QB is charged high through PM2 and NM4 is held off. At the end of the evaluation phase, as the CLK falls low, node X1 remains high and X2 stores the charge dynamically [1].

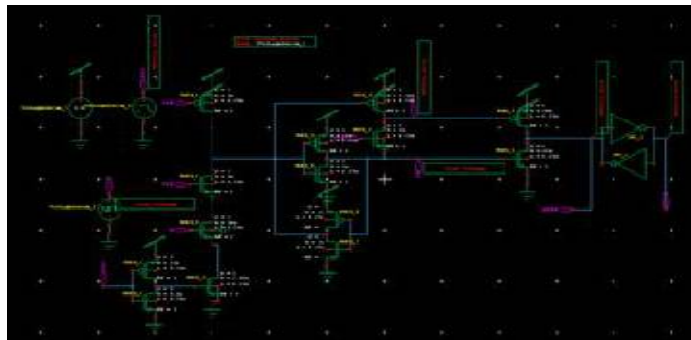


Fig. 4 Proposed DDFF

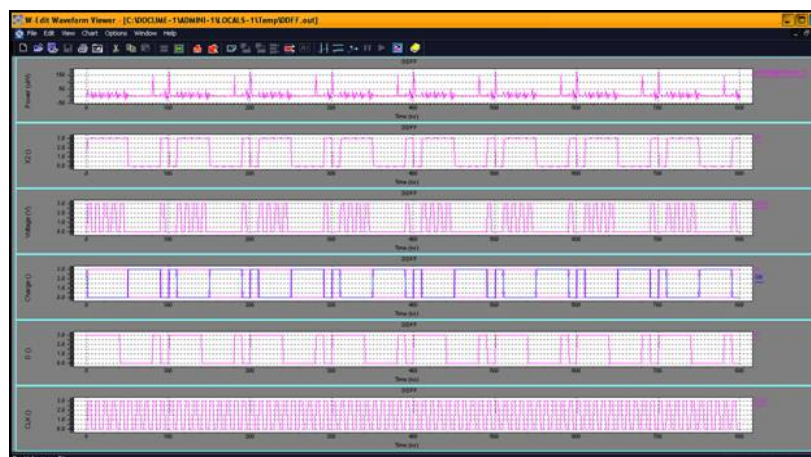


Fig. 5 Waveform of DDFF

Fig. 5 shows waveform of DDFF. The minimum time period before the CLK edge is setup time and the minimum time period after the CLK edge is the hold time, where the data should be stable so that proper sampling is possible. Here setup time and hold time depend on the CLK overlap period.



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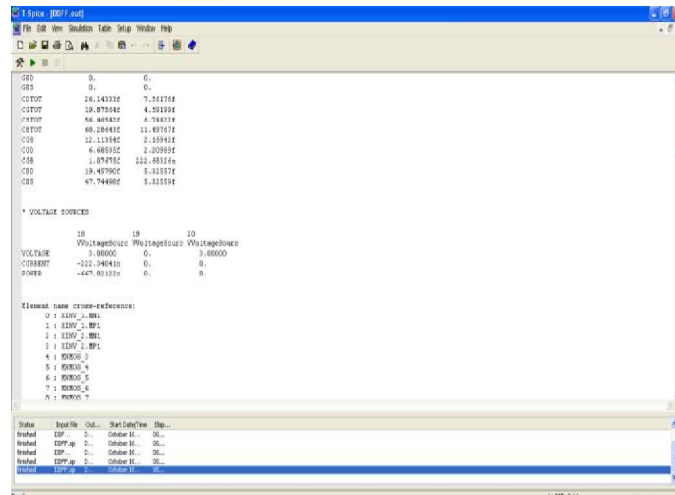


Fig.6 Power Analysis of DDFF

## VI. RESULTS

The Power analysis of DDFF design using 90nm CMOS technology shows that it requires 0.667uW of power. In future DDFF design using Sleepy Stack method achieving ultra low leakage power consumption and offers a power reduction upto 45% which can be use for low power efficiency.

## VII. CONCLUSION

This paper presents a comparative study of different low power design techniques for dual dynamic node hybrid flipflop (DDFF) and embedded logic module based on DDFF by using sleepy stack technique which can achieve smaller transistor delay than the forced stack technique and use for ultra low leakage power consumption. The main advantage of the sleepy stack approach is the ability to use high- V<sub>th</sub> which causes low leakage current and hence results in low leakage power. V<sub>th</sub> of sleepy stack method is 69% higher than that of the forced stack. This higher V<sub>th</sub> can potentially result in large leakage power reduction. Thus it can be used for future IC'S for low power efficiency. The present study provides a proper choice for leakage power minimization technique for a specific VLSI application. Thus sleepy stack technique is a feasible solution for designer in designing low power CMOSVLSI circuit more efficiently.

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